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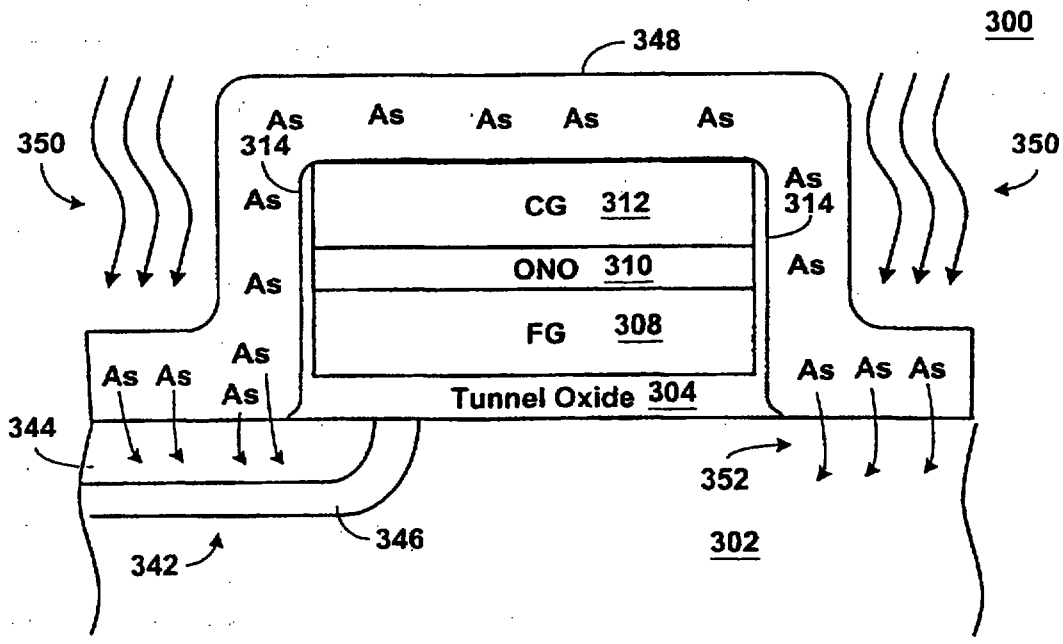
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(54) Title: SOLID-SOURCE DOPING FOR SOURCE/DRAIN OF FLASH MEMORY



(57) Abstract: A method of manufacturing a flash memory device in which minimal gate edge lifting is accomplished by minimally oxidizing the gate stack and exposed surface of the substrate, anisotropically etching the layer of oxide from the substrate, forming a doped solid source material on portions of the substrate in which source regions are to be formed and diffusing the dopants from the solid source material into the substrate.

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